

## 1. General description

Planar passivated AC Thyristor Triac power switch in a SOT428 (DPAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients.

## 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- Direct interfacing with low power drivers and microcontrollers
- Full cycle AC conduction
- Less sensitive gate for high noise immunity
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Sensitive gate for easy logic level triggering
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$

## 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls

## 4. Quick reference data

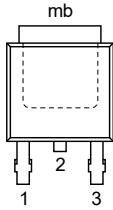
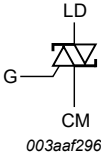
Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 108\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	-	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	-	35	A
		full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	-	39	A
$T_j$	junction temperature		-	-	125	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>PP</sub>	peak pulse voltage	T <sub>j</sub> = 25 °C; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	-	2	kV
<b>Static characteristics</b>						
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	35	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>	-	-	35	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>	-	-	35	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 6 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>	-	-	1.7	V
V <sub>CL</sub>	clamping voltage	I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C	850	-	-	V
<b>Dynamic characteristics</b>						
dV <sub>D</sub> /dt	rate of rise of off-state voltage	V <sub>DM</sub> = 536 V; T <sub>j</sub> = 125 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	1000	-	-	V/μs
di <sub>com</sub> /dt	rate of change of commutating current	V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 20 V/μs; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 10 V/μs; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	10	-	-	A/ms
		V <sub>D</sub> = 400 V; T <sub>j</sub> = 125 °C; I <sub>T(RMS)</sub> = 4 A; dV <sub>com</sub> /dt = 1 V/μs; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	15	-	-	A/ms

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	CM	common	 <p style="text-align: center;"><b>DPAK (SOT428)</b></p>	 <p style="text-align: center;">003aaf296</p>
2	LD	load		
3	G	gate		
mb	LD	mounting base; load		

## 6. Ordering information

Table 3. Ordering information

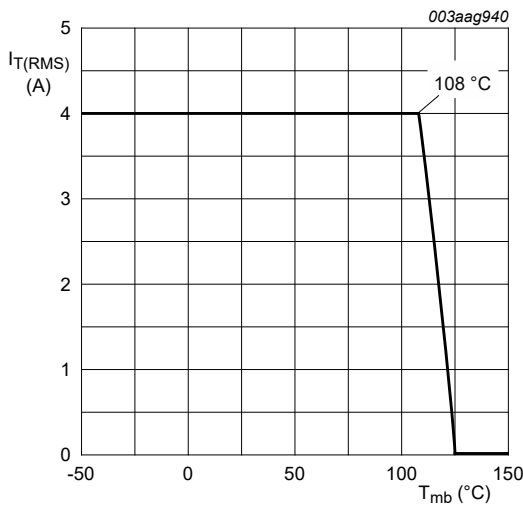
Type number	Package		
	Name	Description	Version
ACTT4S-800C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428

## 7. Limiting values

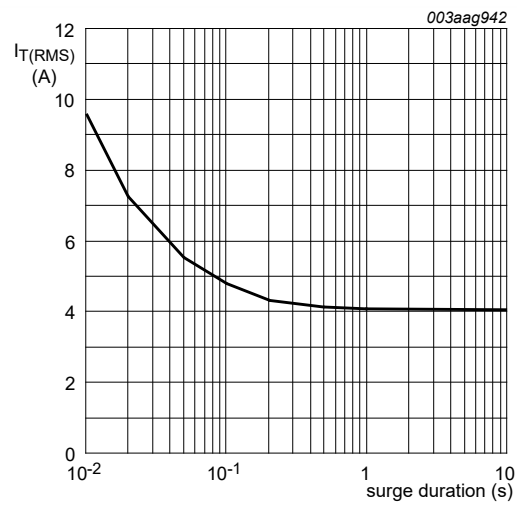
**Table 4. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	800	V
$I_{T(RMS)}$	RMS on-state current	full sine wave; $T_{mb} \leq 108\text{ °C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>	-	4	A
$I_{TSM}$	non-repetitive peak on-state current	full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a>	-	35	A
		full sine wave; $T_{j(\text{init})} = 25\text{ °C}$ ; $t_p = 16.7\text{ ms}$	-	39	A
$I^2t$	$I^2t$ for fusing	$t_p = 10\text{ ms}$ ; sine-wave pulse	-	6	A <sup>2</sup> s
$di_T/dt$	rate of rise of on-state current	$I_G = 70\text{ mA}$	-	100	A/ $\mu$ s
$I_{GM}$	peak gate current	$t = 20\text{ }\mu$ s	-	2	A
$P_{GM}$	peak gate power		-	5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	-	0.5	W
$T_j$	junction temperature		-	125	°C
$V_{PP}$	peak pulse voltage	$T_j = 25\text{ °C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>	-	2	kV



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 108\text{ °C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

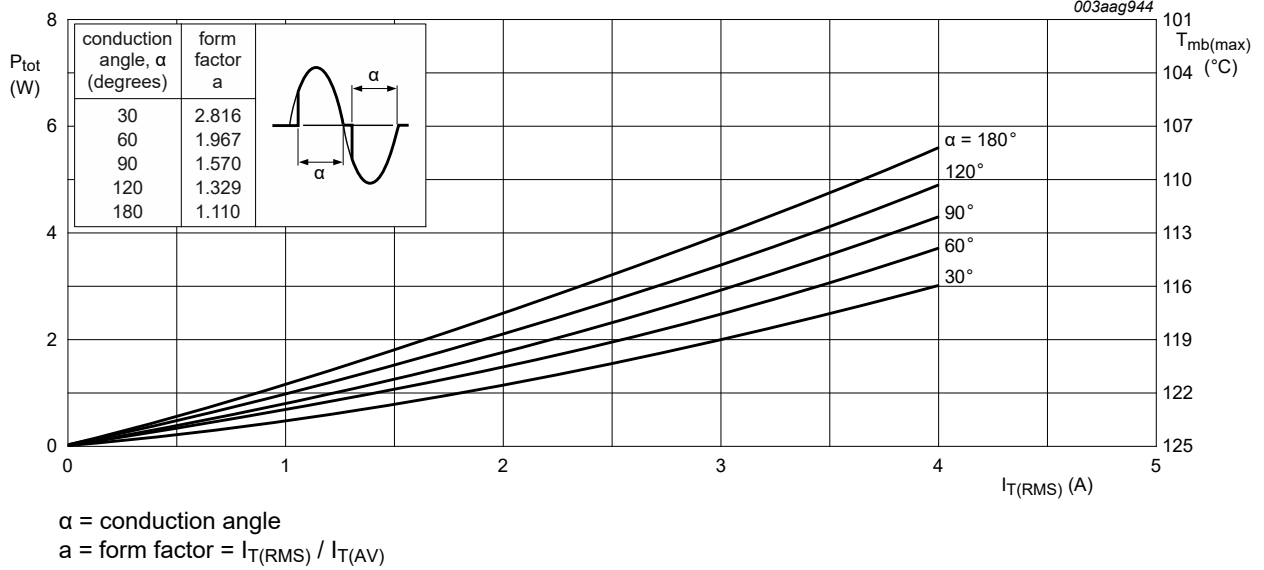


Fig. 3. power dissipation as a function of RMS on-state current; maximum values

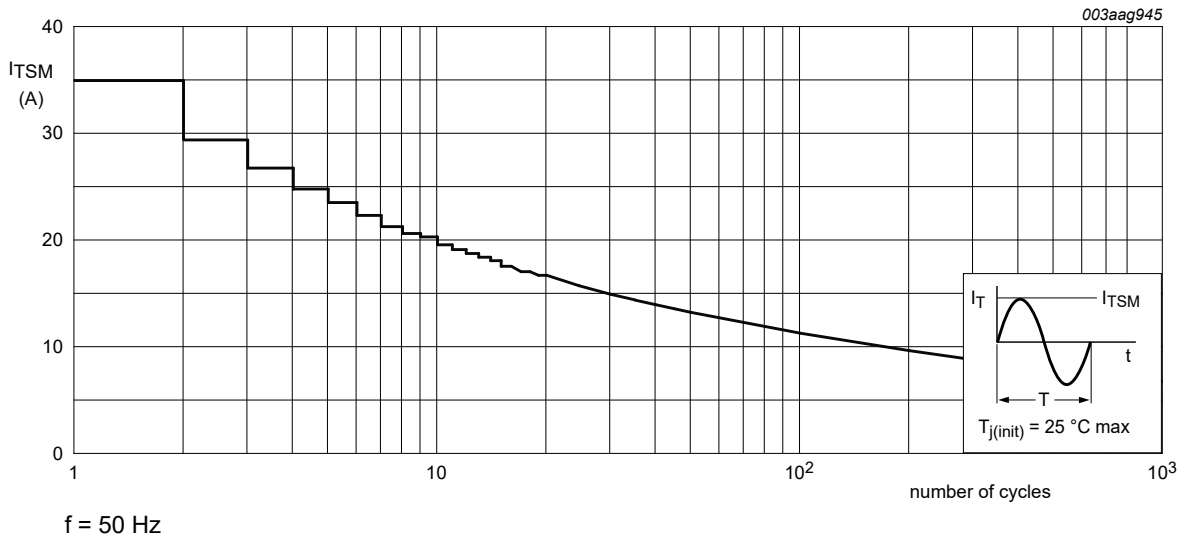


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

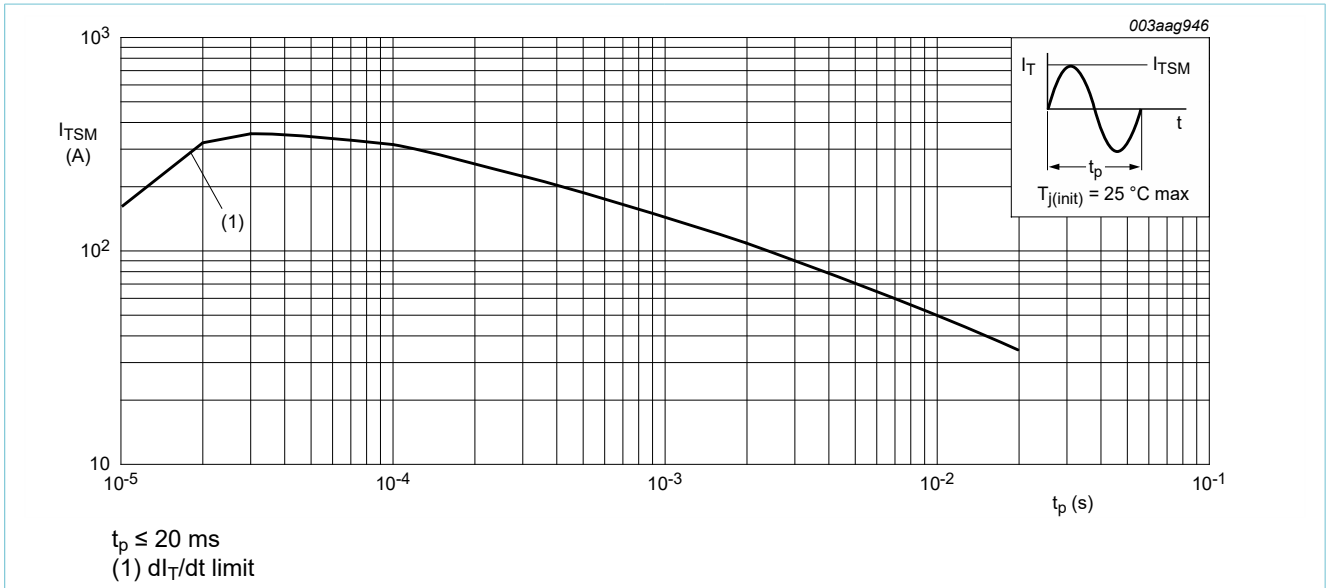


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

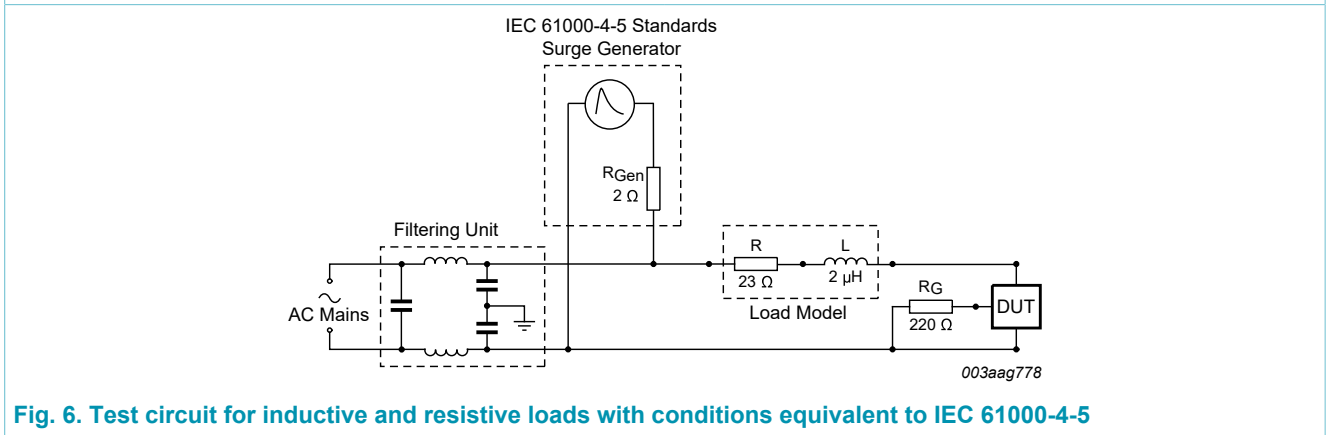
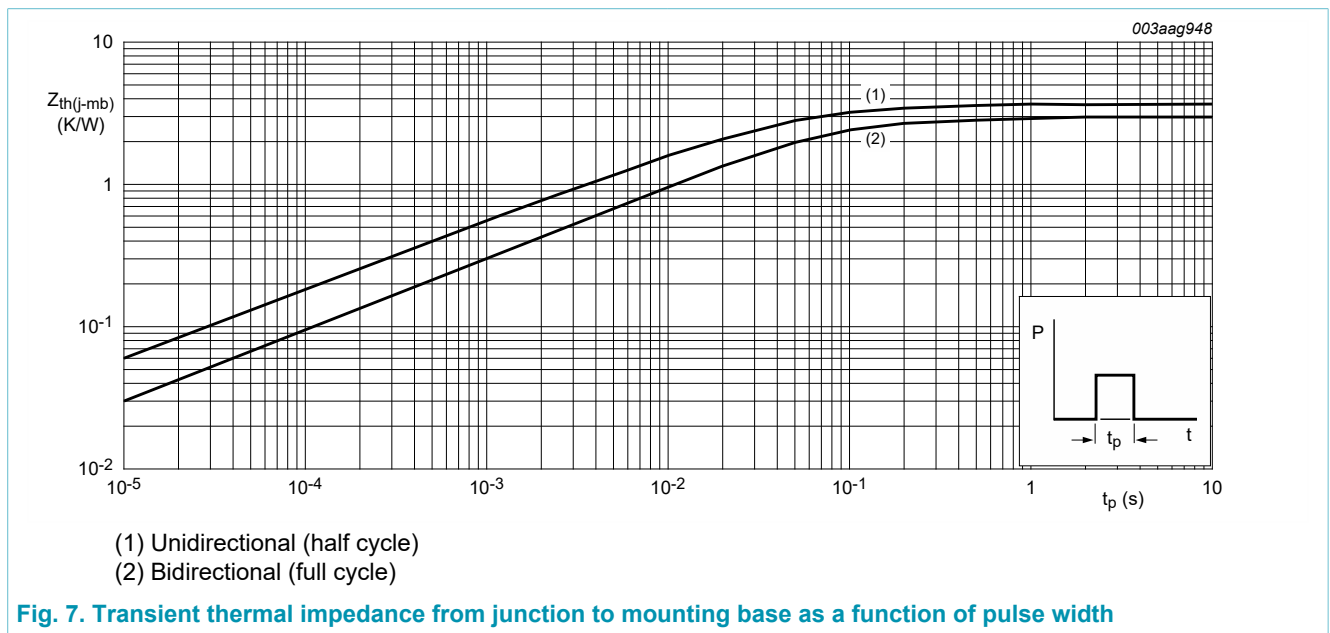


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

### 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	full cycle; Fig. 7	-	-	3	K/W
		half cycle; Fig. 7	-	-	3.7	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	75	-	K/W



## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$I_{GT}$	gate trigger current	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	35	mA
		$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 8</a>	-	-	35	mA
$I_L$	latching current	$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G+; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	50	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD+ G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	60	mA
		$V_D = 12\text{ V}$ ; $I_G = 100\text{ mA}$ ; LD- G-; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 9</a>	-	-	50	mA
$I_H$	holding current	$V_D = 12\text{ V}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 10</a>	-	-	35	mA
$V_T$	on-state voltage	$I_T = 6\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	-	1.7	V
$V_{GT}$	gate trigger voltage	$V_D = 12\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 12</a>	-	0.8	1	V
		$V_D = 400\text{ V}$ ; $I_T = 100\text{ mA}$ ; $T_j = 125\text{ °C}$ ; <a href="#">Fig. 12</a>	0.2	0.45	-	V
$I_D$	off-state current	$V_D = 800\text{ V}$ ; $T_j = 25\text{ °C}$	-	-	10	$\mu\text{A}$
		$V_D = 800\text{ V}$ ; $T_j = 125\text{ °C}$	-	-	0.5	mA
$V_{CL}$	clamping voltage	$I_{CL} = 0.1\text{ mA}$ ; $t_p = 1\text{ ms}$ ; $T_j = 25\text{ °C}$	850	-	-	V
<b>Dynamic characteristics</b>						
$dV_D/dt$	rate of rise of off-state voltage	$V_{DM} = 536\text{ V}$ ; $T_j = 125\text{ °C}$ ; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit; <a href="#">Fig. 13</a>	1000	-	-	V/ $\mu\text{s}$
$dI_{com}/dt$	rate of change of commutating current	$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 20\text{ V}/\mu\text{s}$ ; (snubberless condition); gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	8	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 10\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	10	-	-	A/ms
		$V_D = 400\text{ V}$ ; $T_j = 125\text{ °C}$ ; $I_{T(RMS)} = 4\text{ A}$ ; $dV_{com}/dt = 1\text{ V}/\mu\text{s}$ ; gate open circuit; <a href="#">Fig. 14</a> ; <a href="#">Fig. 15</a>	15	-	-	A/ms



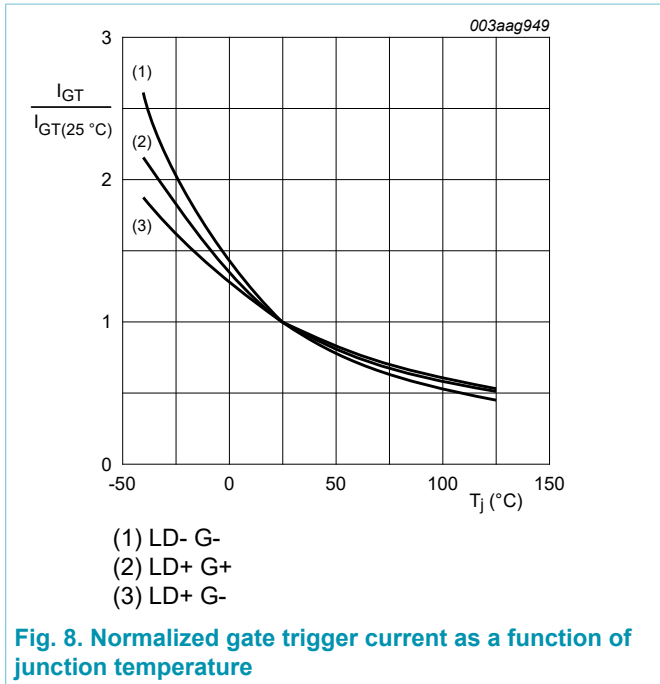


Fig. 8. Normalized gate trigger current as a function of junction temperature

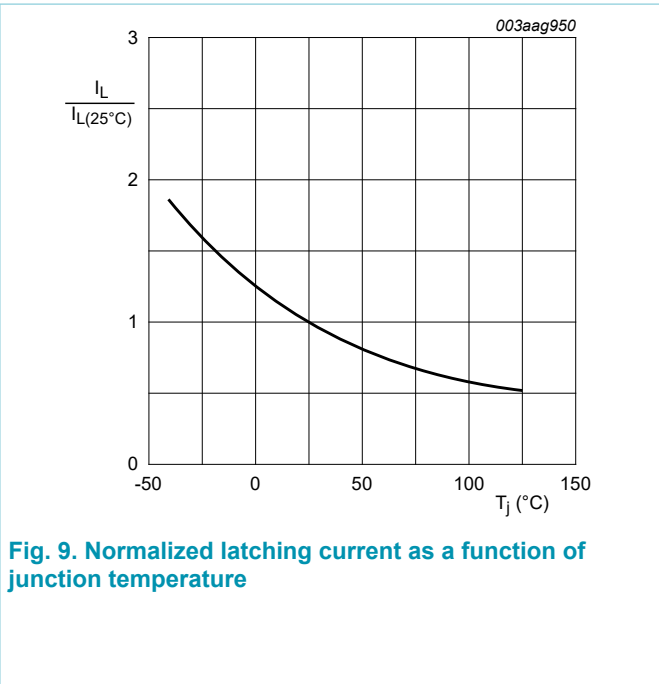


Fig. 9. Normalized latching current as a function of junction temperature

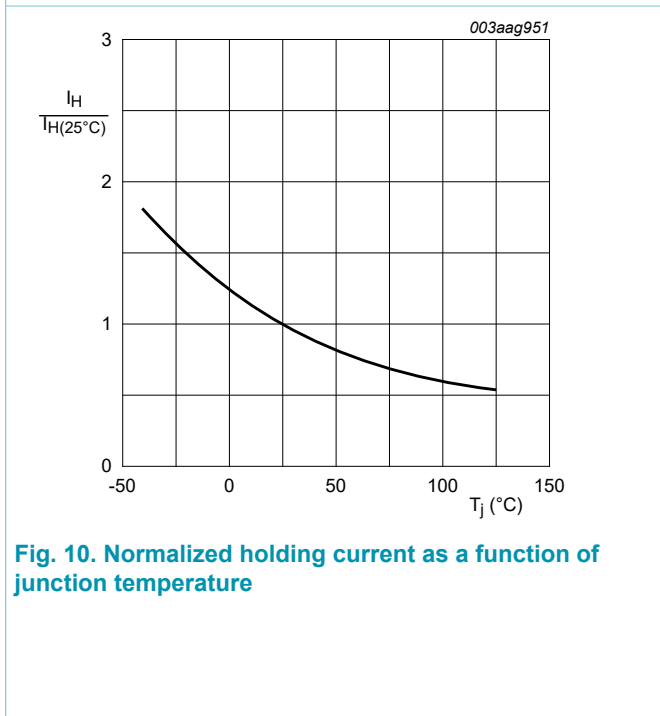


Fig. 10. Normalized holding current as a function of junction temperature

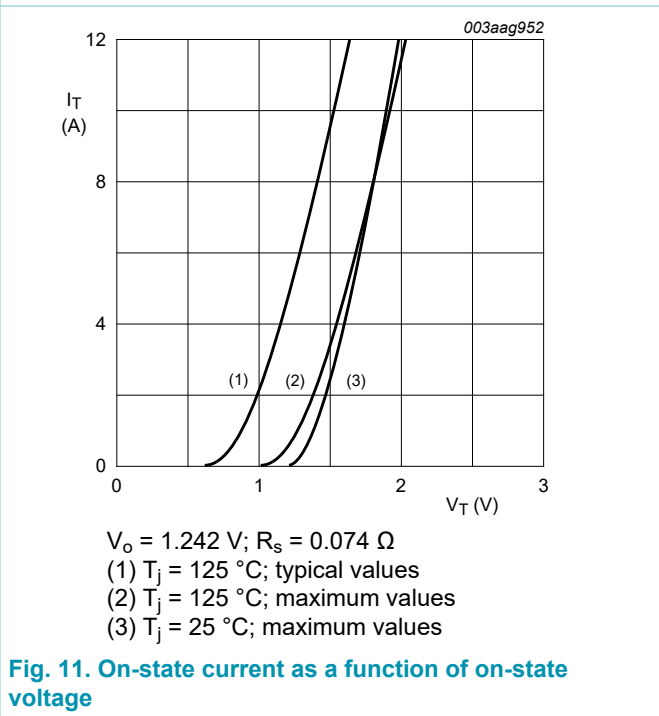


Fig. 11. On-state current as a function of on-state voltage

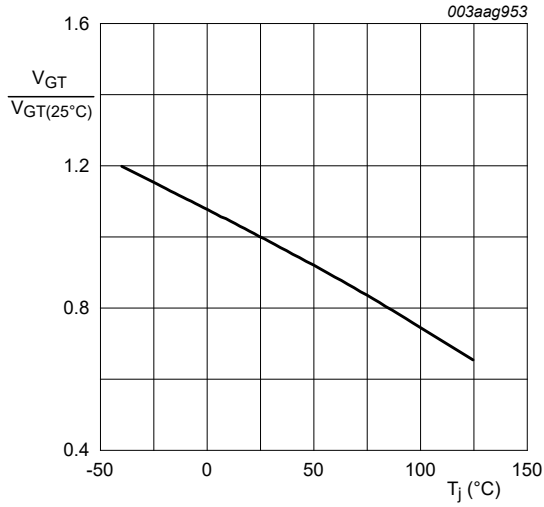
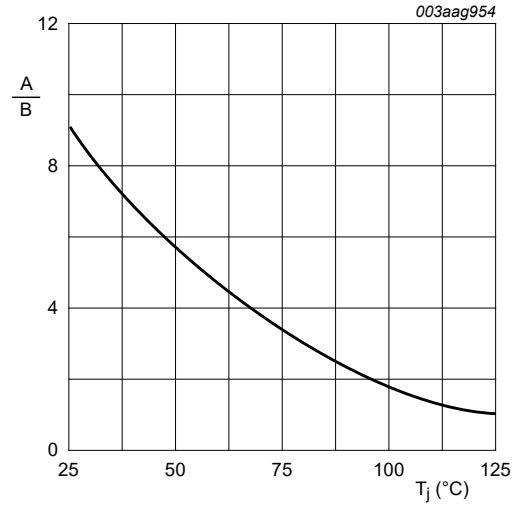
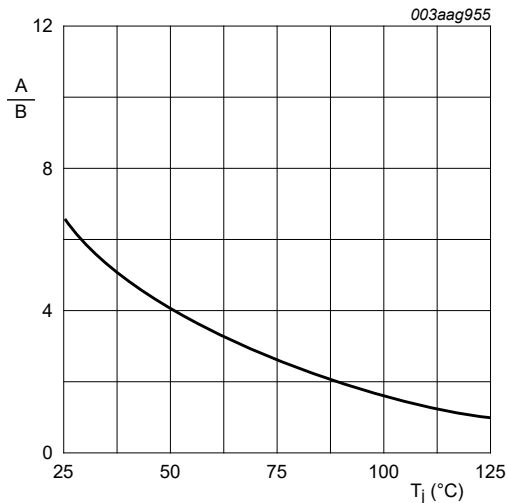


Fig. 12. Normalized gate trigger voltage as a function of junction temperature



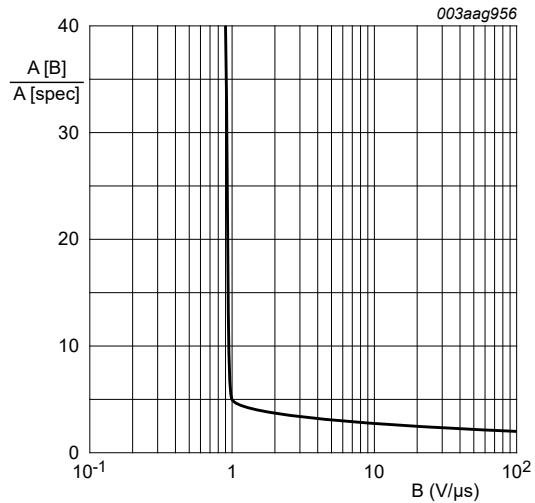
A =  $dV_D/dt$  at condition  $T_j$  °C  
 B =  $dV_D/dt$  at condition  $T_j$  [125] °C

Fig. 13. Normalized rate of rise of off-state voltage as a function of junction temperature



A =  $di_{com}/dt$  at condition  $T_j$  °C  
 B =  $di_{com}/dt$  at condition  $T_j$  [125] °C  
 $V_D = 400$  V

Fig. 14. Normalized critical rate of rise of commutating current as a function of junction temperature



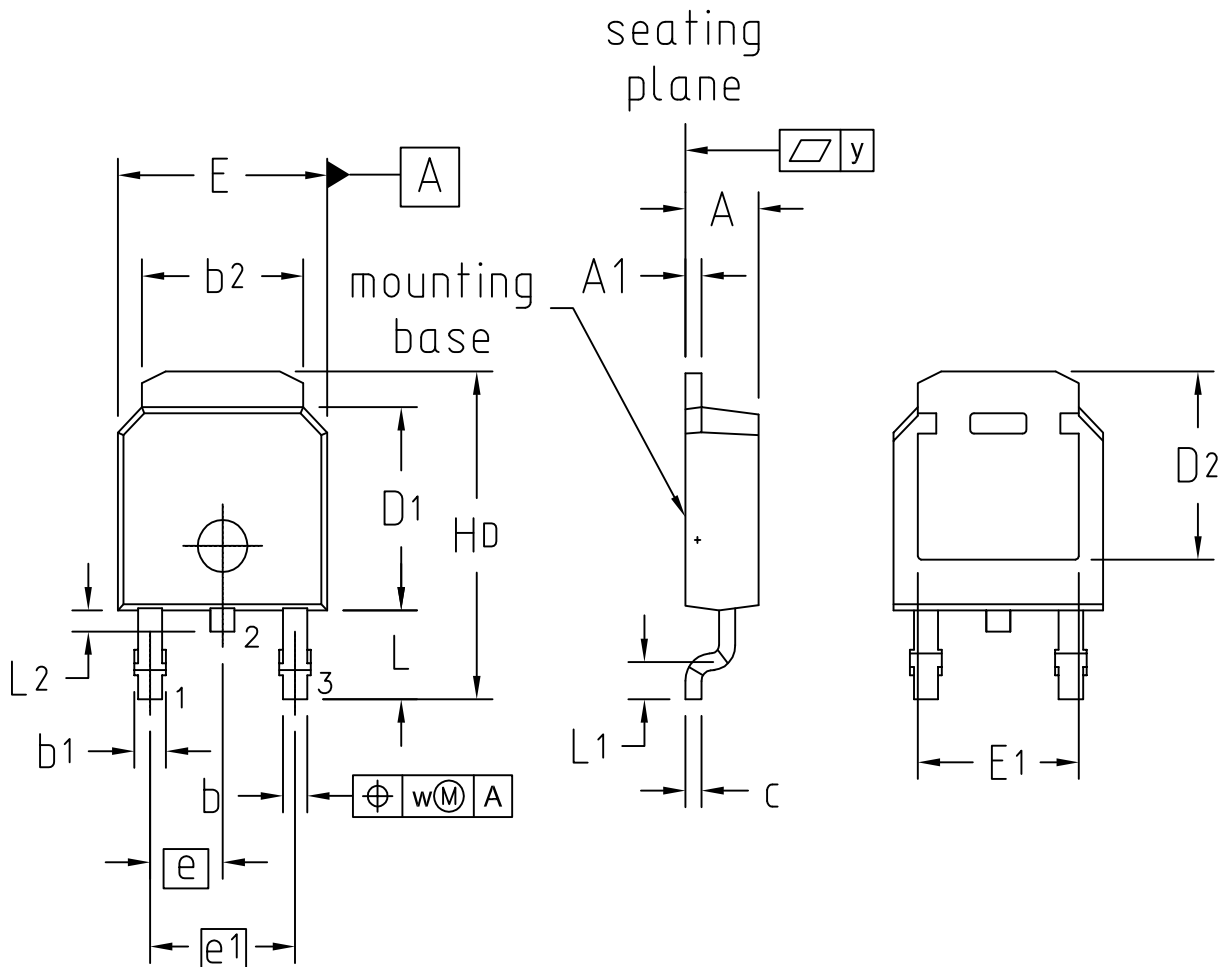
A [B] is  $di_{com}/dt$  at condition B,  $dV_{com}/dt$   
 A [spec] is the specified data sheet value of  $di_{com}/dt$   
 turn-off time < 20 ms

Fig. 15. Normalized critical rate of change of commutating current as a function of critical rate of change of commutating voltage; minimum values

10. Package outline

Plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)

SOT428



UNIT	A	A <sub>1</sub>	b	b <sub>1</sub>	b <sub>2</sub>	c	D <sub>1</sub>	D <sub>2</sub>	E	E <sub>1</sub>	e	e <sub>1</sub>	H <sub>d</sub>	L	L <sub>1</sub>	L <sub>2</sub>	w	y
mm	2.38	0.93	0.89	1.1	5.46	0.56	6.22	4.00	6.73	4.45	2.285	4.57	10.40	2.95	0.5	0.90	0.2	0.20
	2.22	0.46	0.71	0.9	5.00	0.20	5.98	min.	6.47	min.			9.60	2.55	min.	0.50	0.2	max.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT428		TO-252				

Fig. 16. Package outline DPAK (SOT428)

## 11. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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Date of release: 11 October 2016